

# **HAT1090C**

# Silicon P Channel MOS FET Power Switching

R07DS1171EJ0500

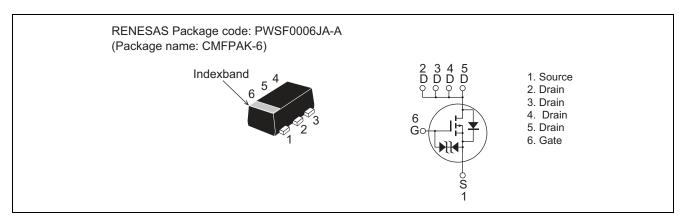
(Previous: REJ03G1228-0400) Rev.5.00

Mar 19, 2014

#### **Features**

- Low on-resistance  $R_{DS(on)} = 50 \text{ m}\Omega \text{ typ. (at } V_{GS} = -4.5 \text{ V})$
- Low drive current.
- 2.5 V gate drive devices.
- High density mounting

#### **Outline**



#### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to Source voltage	$V_{DSS}$	-20	V
Gate to Source voltage	$V_{GSS}$	±12	V
Drain current	I <sub>D</sub>	-2.5	Α
Drain peak current	I <sub>D(pulse)</sub> Note1	-10	Α
Body - Drain diode reverse drain current	I <sub>DR</sub>	-2.5	Α
Channel dissipation	Pch <sup>Note 2</sup>	900	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes 1.  $PW \le 10 \mu s$ , duty cycle  $\le 1\%$ 

2. When using the glass epoxy board. (FR4  $40 \times 40 \times 1.6$ mm), Ta =  $25^{\circ}$ C

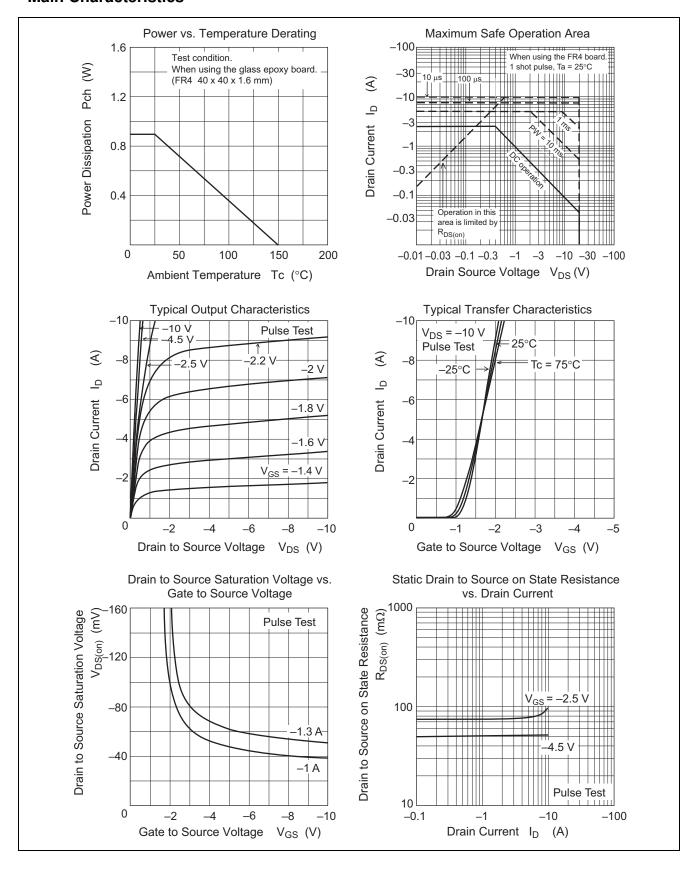
## **Electrical Characteristics**

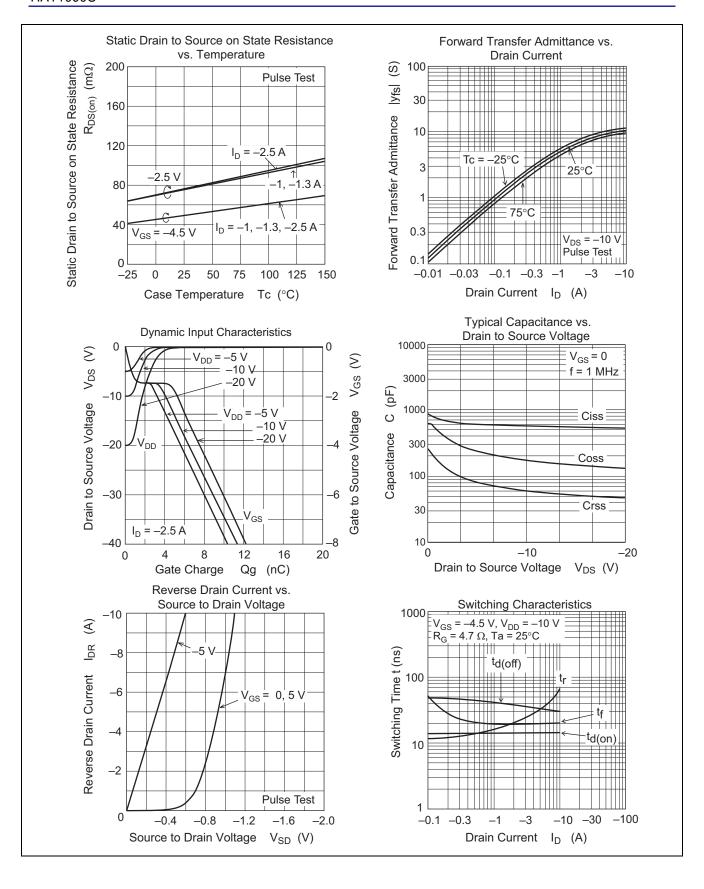
 $(Ta = 25^{\circ}C)$ 

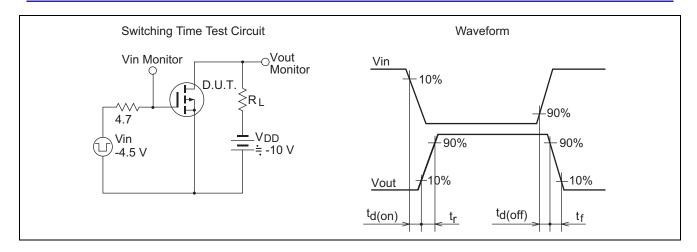
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to Source breakdown voltage	V <sub>(BR)DSS</sub>	-20	_	_	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to Source breakdown voltage	V <sub>(BR)GSS</sub>	±12	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to Source leakage current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$
Drain to Source leakage current	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -20 \text{ V}, V_{GS} = 0$
Gate to Source cutoff voltage	V <sub>GS(th)</sub>	-0.4	_	-1.4	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}^{\text{Note3}}$
Static drain to source on state	R <sub>DS(on)</sub>	_	50	65	mΩ	$I_D = -1.3 \text{ A}, V_{GS} = -4.5 \text{ V}^{\text{Note3}}$
resistance	R <sub>DS(on)</sub>	_	74	104	mΩ	$I_D = -1.3 \text{ A}, V_{GS} = -2.5 \text{ V}^{\text{Note3}}$
Forward transfer admittance	y <sub>fs</sub>	3.5	5.5	_	S	$I_D = -1.3 \text{ A}, V_{DS} = -10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss	_	590	_	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	175	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	60	_	pF	
Total gate charge	Qg	_	7	_	nC	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$ $I_{D} = -2.5 \text{ A}$
Gate to Source charge	Qgs	_	1.2	_	nC	
Gate to Drain charge	Qgd	_	2.5	_	nC	
Turn - on delay time	t <sub>d(on)</sub>	_	15	_	ns	$\begin{split} V_{DS} = -10 \ V, \ V_{GS} = -4.5 \ V, \\ I_{D} = -1.3 \ A, \ R_{L} = 7.7 \ \Omega, \\ R_{g} = 4.7 \ \Omega \end{split}$
Rise time	t <sub>r</sub>	_	17	_	ns	
Turn - off delay time	$t_{d(off)}$	_	40	_	ns	
Fall time	t <sub>f</sub>	_	20	_	ns	
Body - Drain diode forward voltage	$V_{DF}$	_	-0.8	-1.1	V	I <sub>F</sub> = -2.5 A, V <sub>GS</sub> = 0

Notes: 3. Pulse test

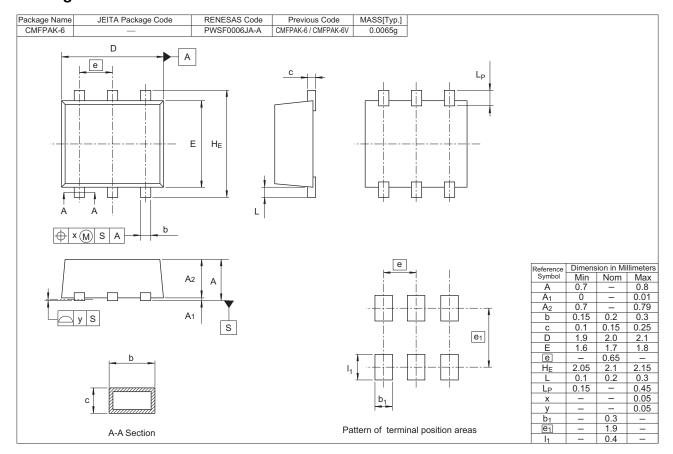
#### **Main Characteristics**







#### **Package Dimensions**



## **Ordering Information**

Orderable Part Number	Quantity	Shipping Container
HAT1090C-EL-E	3000 pcs	Taping

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